

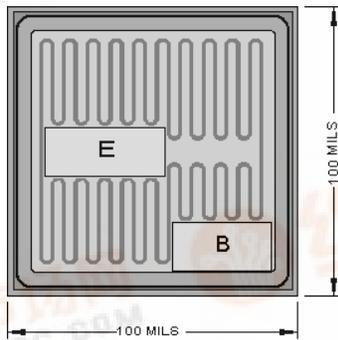


Data Sheet No. 2C5154

**Chip Type 2C5154**  
**Geometry 9201**  
**Polarity NPN**

**Generic Packaged Parts:**

**2N4150, 2N51512, 2N5154,  
 2N5339**



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Chip type **2C5154** by Semicoa Semiconductors provides performance similar to these devices.

**Product Summary:**

**APPLICATIONS:** Designed for medium power amplifier and switching and wide band amplifier applications.

**Part Numbers:**

2N3998, 2N3999, [2N4150](#), [2N4150S](#), [2N5152](#),  
[2N5152L](#), [2N5154](#), [2N5154L](#), 2N5339

**Features:**

- Medium power ratings

**Mechanical Specifications**

<b>Metallization</b>	Top	Al - 37.5 kÅ min.
	Backside	Au - 6.5 kÅ nom.
<b>Bonding Pad Size</b>	Emitter	12 mils x 40 mils
	Base	12 mils x 30 mils
<b>Die Thickness</b>	8 mils nominal	
<b>Chip Area</b>	100 mils x 100 mils	
<b>Top Surface</b>	Silox Passivated	

**Electrical Characteristics**

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
$BV_{CBO}$	$I_C = 10 \text{ mA}, I_E = 0$	80	---	V dc
$I_{CES}$	$V_{CE} = 60 \text{ V}, I_E = 0$	---	1.0	$\mu\text{A}$
$I_{EBO}$	$V_{BE} = 4.0 \text{ V}, I_C = 0$	---	1.0	$\mu\text{A}$
$h_{FE}$	$I_C = 50 \text{ mA dc}, V_{CE} = 5.0 \text{ V}$	50	---	---
$h_{FE}$	$I_C = 2.5 \text{ A dc}, V_{CE} = 5.0 \text{ V}$	70-200	---	---

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.

